

PMPB27EPAX Datasheet

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DiGi Electronics Part Number PMPB27EPAX-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMPB27EPAX

Description MOSFET P-CH 30V 6.1A DFN2020MD-6

Detailed Description P-Channel 30 V 6.1A (Ta) 1.7W (Ta), 12.5W (Tc) Surf

ace Mount DFN2020MD-6



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMPB27EPAX	Nexperia USA Inc.
Series:	Product Status:
TrenchMOS™	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	6.1A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	29mOhm @ 6.1A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2.5V @ 250µA	45 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	1570 pF @ 15 V
FET Feature:	Power Dissipation (Max):
	1.7W (Ta), 12.5W (Tc)
Operating Temperature:	Grade:
-55°C ~ 150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Supplier Device Package:	Package / Case:
DFN2020MD-6	6-UDFN Exposed Pad
Base Product Number:	
PMPB27	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Trench MOSFET technology
- Side wettable flanks for optical solder inspection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- AEC-Q101 qualified

3. Applications

- · Relay driver
- · High-speed line driver
- · High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-	-6.1	Α
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -6.1 A; T_j = 25 °C		-	24	29	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D I
2	D	drain		
3	G	gate	2 5	G LIFE
4	S	source	3 8 94	S
5	D	drain	Transparent top view	017aaa257
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMPB27EPA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB27EPA	4P

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30 V, P-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-6.1	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-3.9	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-25	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
		T _{sp} = 25 °C		-	12.5	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain di	ode					,
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.9	Α
ESD maximum	rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[2]	-	1000	V
Avalanche rugg	jedness					
E _{DS(AL)} S	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = -1.7 A; DUT in avalanche (unclamped)		-	26.8	mJ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Measured between all pins.

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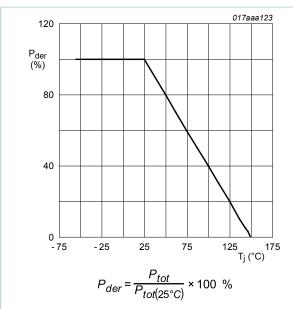


Fig. 1. Normalized total power dissipation as a function of junction temperature

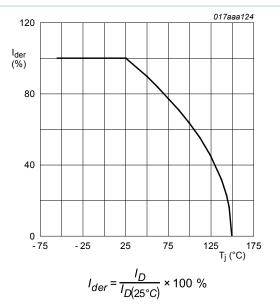
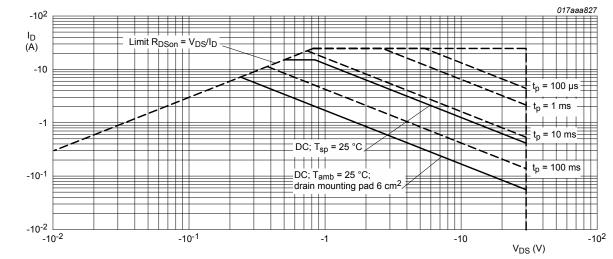


Fig. 2. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uit a)	thermal resistance		[1]	-	235	270	K/W
	from junction to ambient		[2]	-	67	74	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

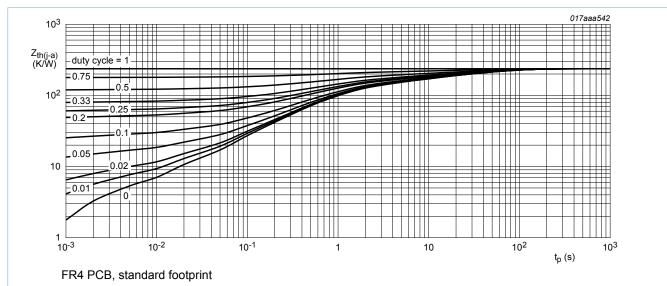


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

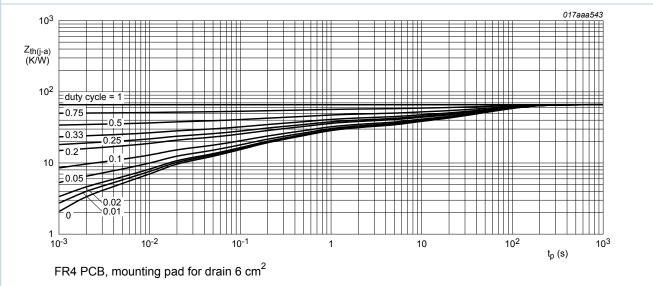


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					,
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-30	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-1	-1.5	-2.5	V
I _{DSS}	drain leakage current	V _{DS} = -30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
I _{GSS} gate leakage current	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -6.1 A; T_j = 25 °C	-	24	29	mΩ
	resistance	V _{GS} = -10 V; I _D = -6.1 A; T _j = 150 °C	-	37	45	mΩ
		V_{GS} = -4.5 V; I_D = -5 A; T_j = 25 °C	-	32	43	mΩ
g _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -6.1 A; T_{j} = 25 °C	-	26	-	S
R _G	gate resistance	f = 1 MHz	-	5.4	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I_{D} = -6.1 A; V_{GS} = -10 V; T_{j} = 25 °C	-	30	45	nC
Q_{GS}	gate-source charge		-	4.8	-	nC
Q_{GD}	gate-drain charge		-	6.3	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	1570	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	170	-	pF
C _{rss}	reverse transfer capacitance		-	150	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -15 V; I _D = -6.1 A; V _{GS} = -10 V;	-	10	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 ^{\circ}C$	-	31	-	ns
t _{d(off)}	turn-off delay time		-	28	-	ns
t _f	fall time		-	19	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	$I_S = -1.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V
t _{rr}	reverse recovery time	I _S = -1.9 A; dI _S /dt = 100 A/μs;	-	14	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = -15 \text{ V}; T_j = 25 \text{ °C}$	-	6	-	nC

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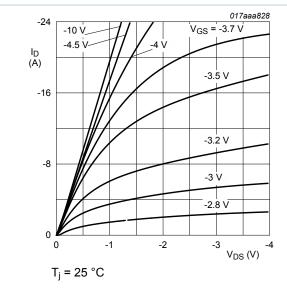


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

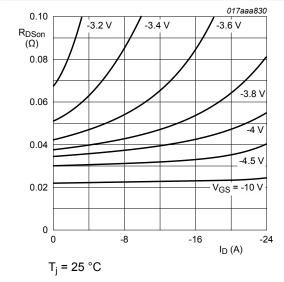


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

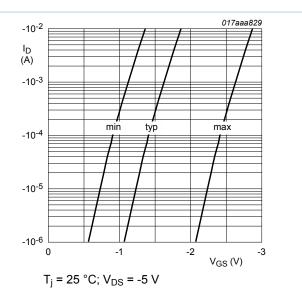


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

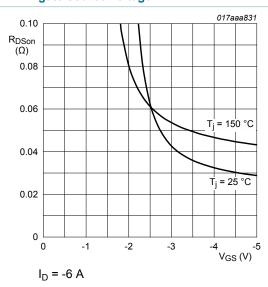


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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30 V, P-channel Trench MOSFET

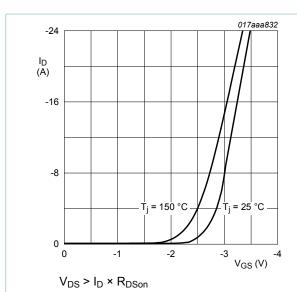


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

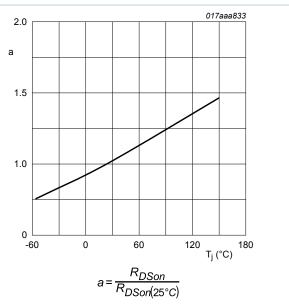


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

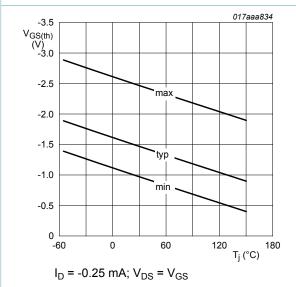


Fig. 12. Gate-source threshold voltage as a function of junction temperature

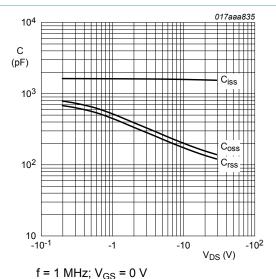


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

values

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8 / 14

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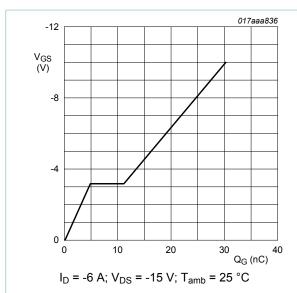


Fig. 14. Gate-source voltage as a function of gate charge; typical values

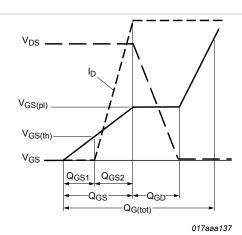


Fig. 15. Gate charge waveform definitions

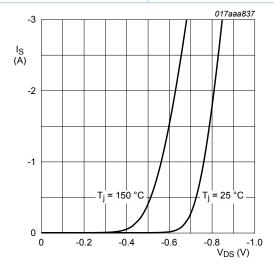
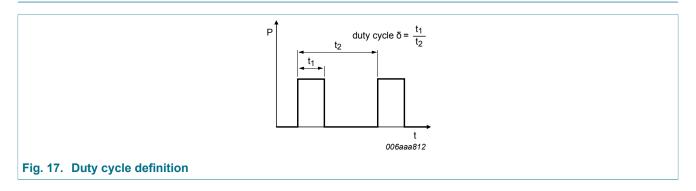


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

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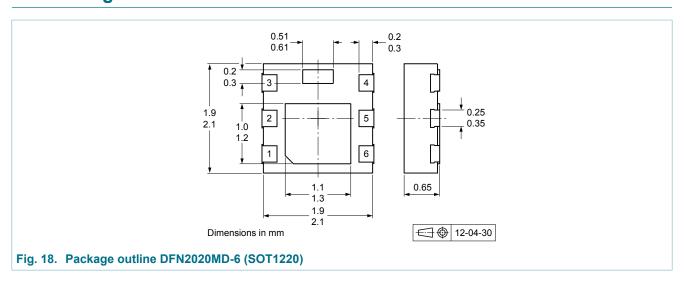
11. Test information



Quality information

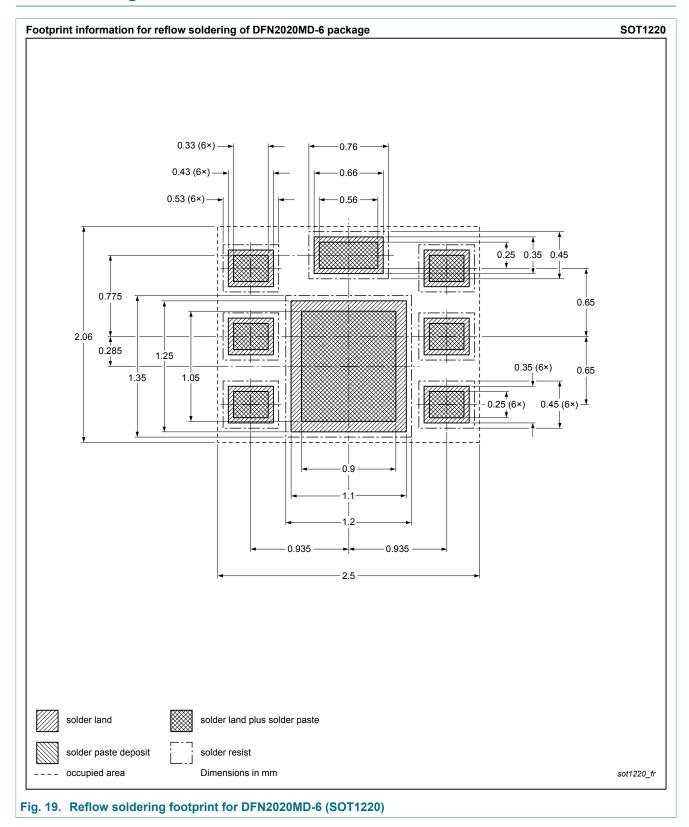
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



30 V, P-channel Trench MOSFET

13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB27EPA v.1	20180327	Product data sheet	-	-

30 V, P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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30 V, P-channel Trench MOSFET

16. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10.	. Characteristics	е
11.	. Test information	10
12.	. Package outline	10
13.	. Soldering	1 1
14.	. Revision history	12
15.	. Legal information	13

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14 / 14

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